

L Number	Hits	Search Text	DB	Time stamp
1	1359	((lower bottom) near electrode) with ((sacrificial oxide) near (layer film)) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 10:35
2	41	((lower bottom) near electrode) with ((sacrificial oxide) near (layer film)) with substrate) and ((contact near (hole via open\$3)) near2 (conductive near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 11:09
3	4	((lower bottom) near electrode) with ((sacrificial near oxide) near (layer film)) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:06
4	923	((sacrificial near oxide) near (layer film)) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 10:42
5	262	((sacrificial near oxide) near (layer film)) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 10:42
6	13	((sacrificial near oxide) near (layer film)) near2 substrate) and ((lower bottom) near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 10:42
7	37	((sacrificial near oxide) near (layer film)) near2 substrate) and (contact near (hole via open\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:01
8	0	((sacrificial near oxide) near (layer film)) near2 substrate) and ((contact near (hole via open\$3)) near2 electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:02
9	1	((fill\$3 near contact near (hole via open\$3)) near2 electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:08
10	2	((contact near (hole via open\$3)) near2 electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:05
11	2	((contact near (hole via open\$3)) with electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:05
12	275	((contact near (hole via open\$3)) and electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:06

13	86	((contact near (hole via open\$3)) and electroplate)) and capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:09
14	26	((contact near (hole via open\$3)) and electroplate)) and capacitor\$1) and ((lower bottom) near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 12:06
15	1	((deposit\$3 fill\$3) near contact near (hole via open\$3)) near2 electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:10
17	1	(deposit\$3 fill\$3) and ((contact near (hole via open\$3)) near2 electroplate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:10
16	267	((contact near (hole via open\$3)) and electroplate)) and (deposit\$3 fill\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:36
18	26	etch\$3 with (gas\$2 near5 (O2 oxygen Cl2 BCl3 Ar HBr) near5 ((top upper) near electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:59
19	2	("6376386").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:39
20	0	etch\$3 with (gas\$2 near2 (O2 oxygen) near5 (Cl2 BCl3 Ar HBr) near5 ((top upper) near electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 13:59